

Hieu Pham Trung Nguyen

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62

papers

1,953

citations

21

h-index

43

g-index

78

ext. papers

2,233

ext. citations

4.1

avg, IF

4.75

L-index

#	Paper	IF	Citations
62	p-Type modulation doped InGaN/GaN dot-in-a-wire white-light-emitting diodes monolithically grown on Si(111). <i>Nano Letters</i> , 2011 , 11, 1919-24	11.5	218
61	One-step overall water splitting under visible light using multiband InGaN/GaN nanowire heterostructures. <i>ACS Nano</i> , 2013 , 7, 7886-93	16.7	162
60	Highly stable photoelectrochemical water splitting and hydrogen generation using a double-band InGaN/GaN core/shell nanowire photoanode. <i>Nano Letters</i> , 2013 , 13, 4356-61	11.5	157
59	Controlling electron overflow in phosphor-free InGaN/GaN nanowire white light-emitting diodes. <i>Nano Letters</i> , 2012 , 12, 1317-23	11.5	157
58	III-Nitride nanowire optoelectronics. <i>Progress in Quantum Electronics</i> , 2015 , 44, 14-68	9.1	152
57	Breaking the carrier injection bottleneck of phosphor-free nanowire white light-emitting diodes. <i>Nano Letters</i> , 2013 , 13, 5437-42	11.5	117
56	Growth of large-scale vertically aligned GaN nanowires and their heterostructures with high uniformity on SiO(x) by catalyst-free molecular beam epitaxy. <i>Nanoscale</i> , 2013 , 5, 5283-7	7.7	75
55	Engineering the carrier dynamics of InGaN nanowire white light-emitting diodes by distributed p-AlGaIn electron blocking layers. <i>Scientific Reports</i> , 2015 , 5, 7744	4.9	74
54	Full-color InGaIn/GaN dot-in-a-wire light emitting diodes on silicon. <i>Nanotechnology</i> , 2011 , 22, 445202	3.4	71
53	High efficiency photoelectrochemical water splitting and hydrogen generation using GaN nanowire photoelectrode. <i>Nanotechnology</i> , 2013 , 24, 175401	3.4	70
52	Color-tunable, phosphor-free InGaIn nanowire light-emitting diode arrays monolithically integrated on silicon. <i>Optics Express</i> , 2014 , 22 Suppl 7, A1768-75	3.3	69
51	Alternating-Current InGaIn/GaN Tunnel Junction Nanowire White-Light Emitting Diodes. <i>Nano Letters</i> , 2015 , 15, 6696-701	11.5	64
50	InN p-i-n Nanowire Solar Cells on Si. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011 , 17, 1062-8	3.8	69
49	Temperature-dependent nonradiative recombination processes in GaN-based nanowire white-light-emitting diodes on silicon. <i>Nanotechnology</i> , 2012 , 23, 194012	3.4	54
48	Highly efficient, spectrally pure 340 nm ultraviolet emission from Al _x Ga _{1-x} N nanowire based light emitting diodes. <i>Nanotechnology</i> , 2013 , 24, 345201	3.4	48
47	Atomic Ordering in InGaIn Alloys within Nanowire Heterostructures. <i>Nano Letters</i> , 2015 , 15, 6413-8	11.5	30
46	High-Efficiency InGaIn/GaN Dot-in-a-Wire Red Light-Emitting Diodes. <i>IEEE Photonics Technology Letters</i> , 2012 , 24, 321-323	2.2	30

45	. <i>IEEE Journal of Quantum Electronics</i> , 2014 , 50, 483-490	2	29
44	Full-Color InGaN/AlGaIn Nanowire Micro Light-Emitting Diodes Grown by Molecular Beam Epitaxy: A Promising Candidate for Next Generation Micro Displays. <i>Micromachines</i> , 2019 , 10,	3.3	22
43	p-Type dopant incorporation and surface charge properties of catalyst-free GaN nanowires revealed by micro-Raman scattering and X-ray photoelectron spectroscopy. <i>Nanoscale</i> , 2014 , 6, 9970-6	7.7	21
42	High efficiency green/yellow and red InGaN/AlGaIn nanowire light-emitting diodes grown by molecular beam epitaxy. <i>Journal of Science: Advanced Materials and Devices</i> , 2017 , 2, 150-155	4.2	21
41	Interplay of strain and indium incorporation in InGaIn/GaN dot-in-a-wire nanostructures by scanning transmission electron microscopy. <i>Nanotechnology</i> , 2015 , 26, 344002	3.4	19
40	Phosphor-Free InGaIn/GaN Dot-in-a-Wire White Light-Emitting Diodes on Copper Substrates. <i>Journal of Electronic Materials</i> , 2014 , 43, 868-872	1.9	15
39	High performance electron blocking layer-free InGaIn/GaN nanowire white-light-emitting diodes. <i>Optics Express</i> , 2020 , 28, 665-675	3.3	15
38	Controlling color emission of InGaIn/AlGaIn nanowire light-emitting diodes grown by molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017 , 35, 02B108	1.3	14
37	Epitaxial Growth and Characterization of AllInN-Based Core-Shell Nanowire Light Emitting Diodes Operating in the Ultraviolet Spectrum. <i>Scientific Reports</i> , 2020 , 10, 2547	4.9	13
36	On the efficiency droop of top-down etched InGaIn/GaN nanorod light emitting diodes under optical pumping. <i>AIP Advances</i> , 2013 , 3, 082103	1.5	13
35	Improving carrier transport in AlGaIn deep-ultraviolet light-emitting diodes using a strip-in-a-barrier structure. <i>Applied Optics</i> , 2020 , 59, 5276-5281	1.7	11
34	Tunable, full-color nanowire light emitting diode arrays monolithically integrated on Si and sapphire 2016 ,		10
33	Engineering the color rendering index of phosphor-free InGaIn/(Al)GaIn nanowire white light emitting diodes grown by molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 02C113	1.3	10
32	Fabrication of Phosphor-Free III-Nitride Nanowire Light-Emitting Diodes on Metal Substrates for Flexible Photonics. <i>ACS Omega</i> , 2017 , 2, 5708-5714	3.9	9
31	Enhancing the light extraction efficiency of AllInN nanowire ultraviolet light-emitting diodes with photonic crystal structures. <i>Optics Express</i> , 2020 , 28, 22908-22918	3.3	9
30	Experimental and numerical optical characterization of plasmonic copper nanoparticles embedded in ZnO fabricated by ion implantation and annealing. <i>Journal of Alloys and Compounds</i> , 2016 , 669, 246-253	5.7	8
29	Improvement of the emission properties from InGaIn/GaN dot-in-a-wire nanostructures after treatment in the flowing afterglow of a microwave N ₂ plasma. <i>Nanotechnology</i> , 2014 , 25, 435606	3.4	8
28	Numerical investigation on the device performance of electron blocking layer free AllInN nanowire deep ultraviolet light-emitting diodes. <i>Optical Materials Express</i> , 2020 , 10, 472	2.6	8

27	Photonic crystal-based permutation switch for optical networks. <i>Photonic Network Communications</i> , 2018 , 35, 90-96	1.7	7
26	Effects of optical absorption in deep ultraviolet nanowire light-emitting diodes. <i>Photonics and Nanostructures - Fundamentals and Applications</i> , 2018 , 28, 106-110	2.6	7
25	Deep red fluoride dots-in-nanoparticles for high color quality micro white light-emitting diodes. <i>Optics Express</i> , 2020 , 28, 26189-26199	3.3	7
24	Controlling Fano resonances in multilayer dielectric gratings towards optical bistable devices. <i>Scientific Reports</i> , 2018 , 8, 16404	4.9	6
23	Polyol Synthesis of Zinc Oxide-Graphene Composites: Enhanced Dye- Sensitized Solar Cell Efficiency. <i>Current Nanomaterials</i> , 2018 , 3, 52-60	1.3	6
22	Fano-induced spontaneous emission enhancement of molecule placed in a cluster of asymmetrically-arranged metallic nanoparticles. <i>Journal of Luminescence</i> , 2016 , 173, 199-202	3.8	5
21	4-Port reciprocal optical circulators employing photonic crystals for integrated photonics circuits. <i>Optik</i> , 2017 , 144, 586-590	2.5	5
20	High-performance nanowire ultraviolet light-emitting diodes with potassium hydroxide and ammonium sulfide surface passivation. <i>Applied Optics</i> , 2020 , 59, 7352-7356	1.7	5
19	Enhanced hole transport in AlGaIn deep ultraviolet light-emitting diodes using a double-sided step graded superlattice electron blocking layer. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2020 , 37, 2564	1.7	5
18	Full-Color III-Nitride Nanowire Light-Emitting Diodes 2019 , 3, 551		5
17	High-performance electron-blocking-layer-free deep ultraviolet light-emitting diodes implementing a strip-in-a-barrier structure. <i>Optics Letters</i> , 2020 , 45, 5125-5128	3	4
16	Nanostructured Optoelectronics: Materials and Devices. <i>Journal of Nanomaterials</i> , 2016 , 2016, 1-2	3.2	4
15	Spectral and spatial contributions to white light generation from InGaIn/GaN dot-in-a-wire nanostructures. <i>Journal of Applied Physics</i> , 2013 , 114, 164305	2.5	3
14	Observation of Fano-like resonance in dual-blade shaped gold nanostructures. <i>Journal Physics D: Applied Physics</i> , 2019 , 52, 045106	3	3
13	InGaIn/GaN dot-in-a-wire: ultimate terahertz nanostructure. <i>Laser and Photonics Reviews</i> , 2015 , 9, 105-118	3	2
12	Molecular beam epitaxial growth and characterization of InGaIn/GaN dot-in-a-wire nanoscale heterostructures: toward ultrahigh efficiency phosphor-free white light emitting diodes 2013 ,		2
11	Preparing nano-hole arrays by using porous anodic aluminum oxide nano-structural masks for the enhanced emission from InGaIn/GaN blue light-emitting diodes. <i>Advances in Natural Sciences: Nanoscience and Nanotechnology</i> , 2012 , 3, 045018	1.6	2
10	Enhanced Efficiency of Dye-Sensitized Solar Cells Based on Polyol-Synthesized Nickel/Zinc Oxide Composites. <i>Journal of Electronic Materials</i> , 2019 , 48, 252-260	1.9	2

9	High-power phosphor-free InGaN/AlGaN dot-in-a-wire core-shell white light-emitting diodes 2015 ,		1
8	Optical phonon modes in InGaN/GaN dot-in-a-wire heterostructures grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013 , 102, 121901	3.4	1
7	Single and double-gate based AlGaIn/GaN MOS-HEMTs for the design of low-noise amplifiers: a comparative study. <i>IET Circuits, Devices and Systems</i> , 2020 , 14, 1018-1025	1.1	1
6	Controlled carrier mean free path for the enhanced efficiency of III-nitride deep-ultraviolet light-emitting diodes. <i>Applied Optics</i> , 2021 , 60, 3088-3093	1.7	1
5	Enhancing Efficiency of AlGaIn Ultraviolet-B Light-Emitting Diodes with Graded p-AlGaIn Hole Injection Layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021 , 218, 2100003	1.6	1
4	Polarization-Engineered p-Type Electron-Blocking-Layer-Free III-Nitride Deep-Ultraviolet Light-Emitting Diodes for Enhanced Carrier Transport. <i>Journal of Electronic Materials</i> , 2022 , 51, 838-846 ^{1.9}		0
3	Correlative Nanoscale Luminescence and Elemental Mapping in InGaIn/(Al)GaIn Dot-in-a-wire Heterostructures 2016 , 815-816		
2	Atomic-Scale Compositional Fluctuations in Ternary III-Nitride Nanowires 2016 , 550-551		
1	2DEG characteristics of InAlAs/InP based HEMTs by solving Schrödinger and Poisson equations followed by device characteristics. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , e2941		1